

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO. 047071-0107

Applicant: Harry A. ATWATER et al.
Title: WAFER BONDED VIRTUAL SUBSTRATE AND METHOD
FOR FORMING THE SAME
Appl. No.: 10/761,918
Filing Date: 01/20/2004
Examiner: Unassigned
Art Unit: 1764

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §1.56

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Submitted herewith on Form PTO/SB/08 a listing of the documents cited by or submitted to the U.S. PTO in parent application Serial No. 10/125,133, filed April 17, 2002. As provided in 37 CFR §1.98(d), copies of the documents are not being provided since they were previously submitted to the United States Patent & Trademark Office in the above-identified parent application.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is determined to be a *prima facie* art reference against the claims of the present application.

TIMING OF THE DISCLOSURE

The listed documents are being submitted in compliance with 37 CFR §1.97(b), before the mailing date of the first Office Action on the merits.

RELEVANCE OF EACH DOCUMENT

The relevance of the documents is explained in the parent application.


Applicants respectfully request that any listed document be considered by the Examiner and be made of record in the present application and that an initialed copy of Form PTO/SB/08 be returned in accordance with MPEP §609.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 CFR §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Respectfully submitted,

Date January 6, 2005

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By 
Leon Radomsky
Attorney for Applicant
Registration No. 43,445

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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Date Submitted: 1/6/05

(use as many sheets as necessary)

Sheet 1 of 7

Complete if Known

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First Named Inventor	Harry A. ATWATER et al.
Group Art Unit	1764
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U.S. PATENT DOCUMENTS

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		Number	Kind Code ² (if known)			
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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	A16	WO	01/03172			01/11/2001		

NON PATENT LITERATURE DOCUMENTS

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	A17	CURTIS et al., "Integration of the UOP/HYDRO MTO Process into Ethylene Plants," 10 th Ethylene Producers' Conference, 1998, pp. 54-85	
	A18	BETT et al., III-V Compounds for Solar Cell Applications, Appl. Phys. A, 1999, pp. 119-129, Vol. 69, Springer-Verlag (published online: 24 June 1999)	
	A19	BRUEL et al., Smart-Cut: A New Silicon On Insulator Material Technology Based on Hydrogen Implantation and Wafer Bonding, March 1997, pp. 1636-1641, Vol. 36, Jpn. J. Appl. Phys	

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	A49	YAMAGUCHI M., Multi-Junction Solar Cells and Novel Structures for Solar Cell Applications, Physica E, 2002, pp. 84-90, Vol. 14, Elsevier Science B.V.	
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	A58	ZAHLER et al., GE Layer Transfer to Si for Photovoltaic Applications, (Presentation), 14 pages, MRS 2001 Spring Conference, (04/2001)	
	A59	ZAHLER et al., Wafer Bonding and Layer Transfer Processes for A 4-Junction Solar Cell, (Presentation) 29 th IEEE Photovoltaic Specialists Conference, New Orleans, USA, (05/2002)	

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				Application Number	10/761,918
				Filing Date	01/20/2004
				First Named Inventor	Harry A. ATWATER et al.
				Group Art Unit	1764
				Examiner Name	Unassigned
				Attorney Docket Number	047071-0107
Sheet	7	of	7		

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A60	ZAHLE et al., Ge/Si Wafer Bonded Epitaxial Templates for GaAs/Si Heterostructures, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
	A61	MORRAL et al., Bonding and Layer Transfer Process of InP on Silicon for the Elaboration of the Bottom Double Heterostructure of 4-Junction High Efficiency Solar Cells, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
	A62	MORRAL et al., Assessment of Optical and Structural Properties of III-V Semiconductors Grown on InP/Si and Ge/Si Wafer Bonded Epitaxial Templates with Application to a Four-Junction Solar Cell, (Abstract), MRS 2003 Spring Meeting, (04/2003)	
	A63	MORRAL et al., Electrical and Structural Characterization of the Interface of Wafer Bonded InP/Si, MRS 2003 Spring Meeting, (04/2003)	
	A64	MORRAL et al., The Role of Hydrogen in H-Induced Exfoliation and Layer Transfer on InP, (Abstract), MRS 2004 Spring Meeting, (04/2004)	

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